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Enhancing the Carrier Transport in Monolayer MoS₂ through Interlayer Coupling with 2D Covalent Organic Frameworks

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The coupling of different two-dimensional materials (2DMs) to form van der Waals heterostructures (vdWHs) is a powerful strategy for adjusting the electronic properties of 2D semiconductors, for applications in opto-electronics and quantum computing. 2D molybdenum disulfide (MoS_2) represents an archetypical semiconducting, monolayer thick versatile platform for the generation of hybrid vdWH with tunable charge transport characteristics through its interfacing with molecules and assemblies thereof. However, the physisorption of (macro)molecules on 2D MoS_2 yields hybrids possessing a limited thermal stability, thereby jeopardizing their technological applications. Herein, we report the rational design and optimized synthesis of 2D covalent organic frameworks (2D-COFs) for the generation of MoS_2 / 2D-COF vdWHs exhibiting strong interlayer coupling effects. The high crystallinity of the 2D-COF films made it possible to engineer an ultrastable periodic doping effect on MoS_2 , boosting devices' field-effect mobility at room temperature. Such a performance increase can be attributed to the synergistic effect of the efficient interfacial electron transfer process and the pronounced suppression of MoS_2 's lattice vibration. This proof-of-concept work validates an unprecedented approach for the efficient modulation of the electronic properties of 2D transition metal dichalcogenides toward high-performance (opto)electronics for CMOS digital circuits.

1. Introduction

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Two-dimensional transition metal dichalcogenides (2D TMDCs) are emerging as prototypical 2D semiconductors for applications in high performance opto-electronic devices. Among them, molybdenum disulfide (MoS_2) is the most explored TMDCs because it combines high mechanical robustness, strong spin-orbit coupling with favorable electronic and optical properties. Such unique characteristics render MoS_2 a promising candidate in both fundamental research and practical applications beyond (opto)electronics in the field of energy conversion and storage as well as chemical and physical sensing^[1]. In particular, the high degree of electrostatic control makes MoS_2 ideal channel material in field-effect transistors (FETs), whose functional complexity can be further enhanced by chemical functionalization, epitomizing a More-than-Moore strategy in the post-silicon era^[2].

However, the recent development of MoS_2 based high-end electronics is still hampered by the significantly limited charge transport properties, e.g., most of the reported electron mobilities (\sim tens of $\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$) in a backgated MoS_2 FETs at room temperature are much lower than the theoretically predicted values ($\sim 410 \text{ cm}^2 \text{V}^{-1} \text{s}^{-1}$)^[3], mainly because of the undesired collective effects of structural defects and the presence of impurities (either environmental or those introduced during the processing), ultimately jeopardizing their applications^[4]. Therefore, improving the charge transport in monolayer MoS_2 via non-invasive approaches is highly sought after.

Passivation by layered hexagonal boron nitride (hBN)^[5], inorganic materials (such as HfO_2 ^[6], Al_2O_3 ^[7], and CaF_2 ^[8]), organic molecule modification or even doping strategy are effective methods to improve TMDCs devices' performances. Compared to the time-consuming dry transfer procedure for hBN and atomic layer deposition (ALD) technique commonly used with inorganic materials, the passivation with small organic molecules represents a simpler, more versatile and cheaper approach. For example, interfacing of TMDCs with organic molecules featuring electron-donating/withdrawing groups can lead

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to doping of the semiconductor through the controlled local modification of its surface potential ^[9]. More importantly, the doping intensity can be amplified via cooperative effects when molecules self-assemble onto 2DMs nanosheets into ordered supramolecular structures ^[10]. However, 2D supramolecular structures held together by non-covalent interactions undergo dynamic rearrangements upon humidity or high temperature exposure ^[11], which lead to instabilities in 2DM-based (opto)electronic devices under operation. In this regard, the use of more robust interactions tethering the molecular units into crystalline films with long-range order is highly desirable.

Two-dimensional covalent organic frameworks (2D-COFs) are a new class of crystalline organic materials composed of 2D polymer sheets featuring an ordered structure, defined porosity, high surface area, and easy chemical tunability ^[12]. 2D-COFs thin films with long-range order along the in-plane directions are particularly appealing and can be produced via interfacial synthesis where the reaction is constrained in a two-dimensional space ^[13]. Unlike self-assembled structures, COFs exhibit much higher thermal and chemical stability owing to the covalent nature of their architectures. The great variety of starting building units and covalent linkages enables the bottom-up engineering of the COF surface areas, pore sizes, and crystal structure. During the initial stages of development, various COFs with reasonable conductivities were generated exploiting organic nodes connected by B-O bonds ^[14]. However, the incorporation of conductive and conjugated ligand units in these B-O linked 2D-COFs resulted in a limited range of conductivities that are still lower than those achieved by other high-performance conducting polymers. In 2011, the development of conductive 2D-COF with imine linkages was reported as COF-366^[15], which was found to provide carrier mobilities that were almost as good as polycrystalline silicon. Since then, other bond connections such as triazine, hydrazine, and azine linkages have been explored to synthesize 2D-COFs with improved electrical conductivities.

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These linkages typically contain heteroatoms, which contribute to the structural polarity of the 2D-COFs. This bond polarization has a significant impact on the stacking behavior of the layered sheets in 2D-COFs, ultimately affecting their charge transport performance. Overall, conjugated 2D-COFs are not ideal as transport layers since most of them are wide band-gap semiconductors, however by taking into account their well-defined structural features in combination with their good mechanical stiffness^[16], their hybridization with a 2D semiconductor can represent a powerful strategy to exploit their chemical programmability for realizing a novel generation of robust hybrid organic/inorganic van der Waals heterostructures (vdWHs)^[17].

In this work we have synthesized imine-based 2D-COFs via Schiff-base reaction at the water/air interface^[18] and transferred them onto monolayer MoS₂ flakes. The charge carrier density of MoS₂ enhanced significantly through the interlayer coupling with 2D-COFs, exceeding 10¹² e⁻/cm². Density functional theory (DFT) calculations revealed an upward shift of MoS₂'s Fermi level (E_F) thereby indicating the efficient charge transfer from 2D-COF film to MoS₂. More importantly, temperature dependent photoluminescence (PL) spectra suggest that the coupling with 2D-COFs is accompanied with a decrease in the optical phonon energy of MoS₂, which demonstrates the suppression of the phonon-electron scattering effects in MoS₂ lattice in the vdWHs, leading to a larger population of free carriers. Overall, the synergistic effect of the efficient electron transfers and the suppression of MoS₂'s lattice vibration contributes to the boosting of the electron mobility^[19] at room temperature in our MoS₂/2D-COF hybrid heterostructures.

2. Results and discussion

2.1. 2D-COF thin film synthesis and characterization

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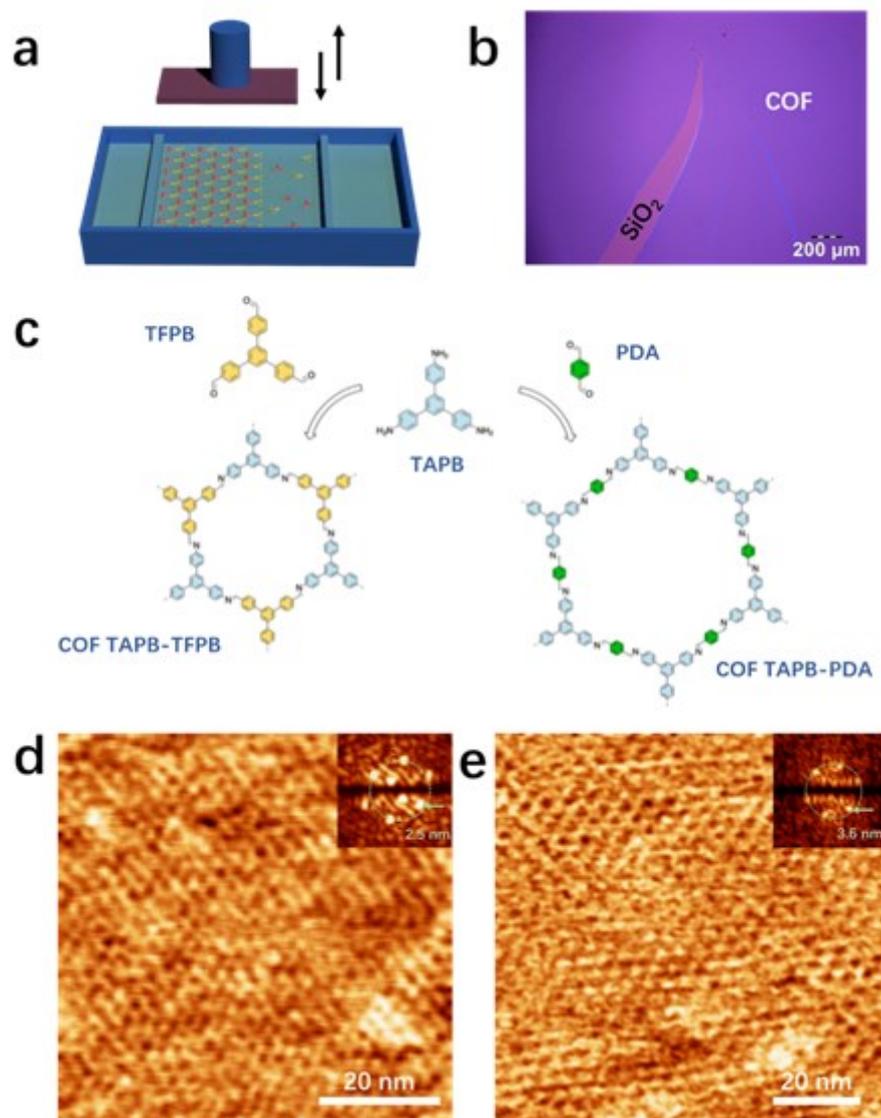


Figure 1. (a) Schematic illustration of the 2D-COF film synthesis and the Langmuir–Schaefer (LS) transfer method. (b) Optical microscopy image of the 2D-COF TAPB-PDA film deposited onto Si/SiO₂ substrate. (c) Chemical structures of 2D-COF TAPB-TFPB and 2D-COF TAPB-PDA. (d, e) Constant current STM image of 2D-COF TAPB-TFPB (d) and 2D-COF TAPB-PDA (e) film on Au (111) surface. Tunneling parameters: (d) tip bias voltage (V_t) = 500 mV, average tunneling current (I_t) = 60 pA; (e) V_t = 365 mV, I_t = 60 pA.

The imine-linked 2D-COF thin films were synthesized at water-air interface by combining the 1,3,5-

tris(4-aminophenyl)benzene (TAPB) unit with 1,3,5-tris(4-formylphenyl)benzene (TFPB)^[20] or terephthalaldehyde (PDA)^[21]. Solutions of the two monomers in chloroform were spread onto water surface in a Langmuir trough and then compressed by means of movable lateral barriers. The water subphase contained scandium trifoliate acting as catalyst for the Schiff-base reaction^[22] (Figure S1). The free-standing 2D-COF films were transferred by the Langmuir-Schaefer (LS) method onto a Si/SiO₂ substrate, as shown in **Figure 1a**. The transferred 2D-COF films were rinsed with water and isopropanol to remove the excess of catalyst and unreacted monomers. **Figure 1b** portrays the optical microscopy image of the homogenous 2D-COF TAPB-PDA film featuring a crack formed during the transfer process. Topographic atomic force microscopy (AFM) images of the film edge revealed a thickness of 3.7 nm and 3.6 nm for the 2D-COF TAPB-TFPB and 2D-COF TAPB-PDA films, respectively (Figure S2). Due to the tip-sample convolution effect and surface roughness of substrate (~ 0.1 nm for SiO₂), the film thickness measured by AFM is typically higher (~ 0.8 nm) than the theoretical value (~ 0.47 nm)^[23] of a MoS₂ monolayer^[16b, 22]. The environmental humidity ($\sim 60\%$) also affected the thickness in AFM measurements, as high relative humidity leads to a large adhesion force between the tip and hydrophilic surface^[24]. We estimated that our 2D-COF films were about 5 atomic layers' thick. Moreover, the few-layer thick 2D-COF films displayed an extremely flat surface with a root mean square roughness (R_{RMS}) of 0.237 nm and 0.278 nm as estimated on 100 μm^2 area, for 2D-COF TAPB-TFPB and 2D-COF TAPB-PDA, respectively. Remarkably, our 2D-COF films have good thermal stability, with unchanged structure after annealing at 520K ^[25]. The small roughness made our 2D-COF films good candidates for building vdWHs though their interfacing with 2D materials. The obtained 2D-COF thin films were found being robust enough during the transfer steps covering almost the entire transmission electron microscope (TEM) grids, showcasing their excellent mechanical robustness

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(Figure S3). As the freestanding 2D-COF thin films were highly sensitive to the electron beam irradiation, the TEM samples got deteriorated rapidly and no high-resolution image of the ordered structure could be acquired. To enhance the radiation resistance of the 2D-COF films, a sandwich structure of 2D-COF film encapsulated in-between two layers of chemical vapor deposition (CVD) graphene was assembled. To this end, selected area electron diffraction (SAED) was performed with low dose diffraction technique. As shown in Figure S4, two rings composed of clear diffraction spots were observed from the sandwich structured samples. The diffraction spots at around 8.1 nm^{-1} and 4.5 nm^{-1} were attributed to the reflections of (110) graphene and the cavity of the benzene units^[16b], suggesting a high degree of order within the 2D-COF films. The porous crystalline structure of 2D-COF films physisorbed on Au (111) substrate was monitored with a sub-nm resolution by scanning tunneling microscopy (STM). Both 2D-COF films exhibited highly ordered in-plane structure, as shown in **Figure 1d and 1e**. The fast Fourier transform (FFT) pattern revealed that the superlattice structure possessing a six-fold symmetry with a periodicity of $\sim 2.5 \text{ nm}$ and $\sim 3.6 \text{ nm}$ for 2D-COF TAPB-TFPB and 2D-COF TAPB-PDA, respectively. Moreover, the film rigidity was studied by AFM in force volume spectroscopy (Figure S7), revealing that 2D-COF TAPB-TFPB film with a smaller periodicity exhibits a greater rigidity when compared to the 2D-COF TAPB-PDA film.

X-ray photoelectron spectroscopy (XPS) investigations were performed to gain insight into the chemical composition of the 2D-COF films.^[26] The analysis of the N 1s peak (Figure S8) confirmed that the N-NH₂ peak at $\sim 399.5 \text{ eV}$ was highly reduced after Schiff-base condensation reaction. Meanwhile, the emergence of N-N=C Peak at $\sim 398.8 \text{ eV}$ indicated the formation of the target imine bond. The presence of a shoulder peak at higher energy level $\sim 400.5 \text{ eV}$ can be ascribed to X-ray-oxidized nitrogen. By integrating the XPS peak areas, the yield of polymerization was estimated as 87% and 83%

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for the 2D-COF TAPB-PDA and the 2D-COF TAPB-TFPB, respectively. Moreover, surface-enhanced Raman scattering (SERS) spectroscopy was employed to gain additional information on the chemical structure of the obtained thin 2D-COF films^[27] (Figure S9). Compared with the building monomers, an additional shoulder peak appeared at $\sim 1550\text{ cm}^{-1}$, near to the C=C vibration peak at $\sim 1600\text{ cm}^{-1}$ in case of both 2D-COF films, which can be attributed to the stretching vibration of the newly formed C=N bonds^[27a]. Therefore, XPS and SERS results provided clear evidence for the formation of the targeted imine bond.

2.2. vdWHs formation and the interlayer charge transfer process

Triangular CVD-grown MoS₂ flakes on sapphire substrate were first transferred onto a Si/SiO₂ substrate using polystyrene as supporting layer^[28] (Figure S10). The vdWHs were obtained by super-imposing the 2D-COF films directly onto the monolayer MoS₂ flakes (**Figure 2a**). AFM analysis revealed a complete coating of the monolayer MoS₂ triangle flakes with the 2D-COF film yielding the vdWHs (Figure S11).

The formation of a hybrid organic-inorganic vdWHs allowed to finely tune the interfacial coupling between the adjacent layers, yielding a modulation of the electronic properties of the employed 2D materials. Compared with randomly physisorbed molecules, a tightly packed crystalline 2D-COF layer guaranteed maximal interference on the band structure of MoS₂ via collective effects, by means of uniform doping. The energy levels of the frontier orbitals of these two 2D-COF films were studied by cyclic voltammetry (CV) measurements and compared to the results of UV-vis spectra (Figure S12). The measured electrochemical bandgap of 2D-COF films was quite similar to the optical bandgap. In particular, the HOMO/LUMO levels of the 2D-COF films resulted -5.32 eV/-2.44 eV and -5.28 eV/-2.62 eV for TAPB-TFPB and TAPB-PDA 2D-COFs, respectively. Conversely the valence band (VB) and

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conduction band (CB) of monolayer MoS₂ amount to -5.76 eV and -4.06 eV. Hence, in view of the higher electron affinity of the 2D semiconductor, an electron transfer from both 2D-COF films to the MoS₂ can be expected. Indeed, Raman and PL spectroscopies (Figure S14)^[29] provide unambiguous evidence for the occurrence of such charge transfer. In particular, Raman spectra recorded at room temperature revealed that the out-of-plane vibration (A_{1g}) peak of MoS₂ shifts towards a lower energy region in the vdWHs, while the in-plane vibration (E_{2g}^1) mode location remains constant (**Figure 2b**). The E_{2g}^1 mode at 386 cm⁻¹ and A_{1g} mode at 404 cm⁻¹ displayed < 20 cm⁻¹ difference, confirming a monolayer nature of MoS₂. We normalized the intensity of E_{2g}^1 peaks and compared the change of the of A_{1g} peak positions between pristine MoS₂ and vdWHs. The interfacing of the 2D semiconductor with 2D-COF TAPB-PDA resulted in ~ 1 cm⁻¹ redshift of the A_{1g} peak with a decrease in peak intensity, indicating the occurrence of charge transfer occurs from the 2D-COF film to the MoS₂ layer (n-doping effect). A similar phenomenon was observed in MoS₂ / 2D-COF TAPB-TFPB vdWHs, where the changes of A_{1g} peak position were found being more pronounced (~ 1.1 cm⁻¹), indicating a higher surface electron concentration of MoS₂. The electron doping level of monolayer MoS₂ can be quantified via low temperature PL spectra. With the decreasing temperature the electron-phonon scattering in MoS₂ crystal lattice became weaker, yielding a more pronounced photoluminescence from localized exciton emission. For a typical PL spectrum of monolayer MoS₂ at 77K (**Figure 2c**), a strong emission feature associated with the optical transitions between the highest valence band and the conduction band at the K-points referred to as the ground state A-exciton emission at ~ 1.90 eV. Because of the spin-orbit splits of the valence band, secondary emission peak with weaker intensity appeared at a higher energy ~ 2.10 eV, which is referred to as the B-exciton peak. The A-exciton peak could be deconvoluted into three peaks after Lorentzian fitting, including defect-related peak at a lower energy ~ 1.76 eV, neutral

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exciton (X) at ~ 1.91 eV and trion peak (X^-) at ~ 1.88 eV. The negatively charged trion was formed upon photogenerated exciton binding to free electron with a binding energy around 30 meV.^[30] Hence, the spectral weight of trion was related to the doping level of MoS₂. As shown in Figure 2c-e, the presence of 2D-COF films increased the trion weight by 9% and 15% in the case of COF TAPB-PDA and TAPB-TFPB vdWHs, respectively, featuring a characteristic n-type doping effect.

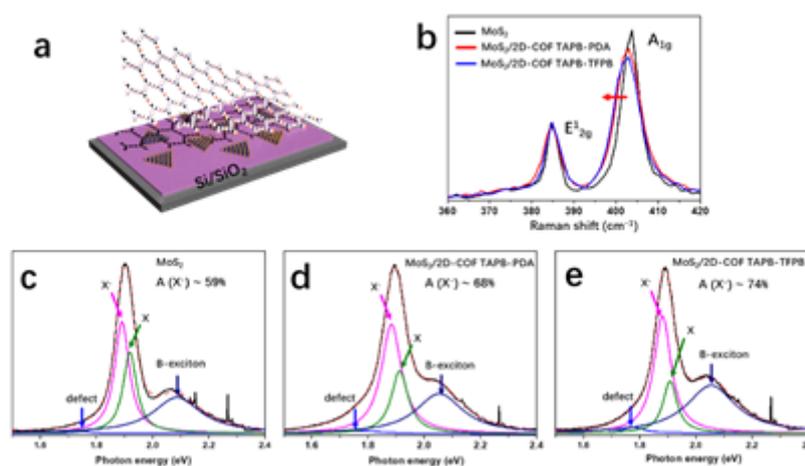


Figure 2. (a) Schematic representation of MoS₂ / 2D-COF vdWH formation. (b) Raman spectra of bare MoS₂ and vdWHs measured at room temperature. Photoluminescence (PL) spectra at 77 K of (c) bare MoS₂, (d) MoS₂ / 2D-COF TAPB-TFPB vdWH, (e) MoS₂ / 2D-COF TAPB-PDA vdWH, fitted with a Lorentzian function to quantify the trion (X^-) weight at 1.88 eV.

The doping of MoS₂ resulting from its interfacing with the 2D-COFs was further confirmed by XPS measurements. Figure S15 compares the binding energies of Mo 3d and S 2p core levels for pristine MoS₂ monolayer and two MoS₂/2D-COF vdWHs. The binding energies of both elements resulted being shifted upwards by about 0.1 eV in MoS₂/2D-COF TAPB-PDA heterostructure, and about 0.2 eV in MoS₂/2D-COF TAPB-TFPB heterostructure. The upward shift of binding energy indicated that MoS₂'s

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Fermi level moves toward the conduction band [31]. Our XPS characterizations further demonstrated the n-type doping effect of MoS₂ in the vdWHs, corroborating the Raman and PL results.

2.3. Electrical characterization and band structure simulation

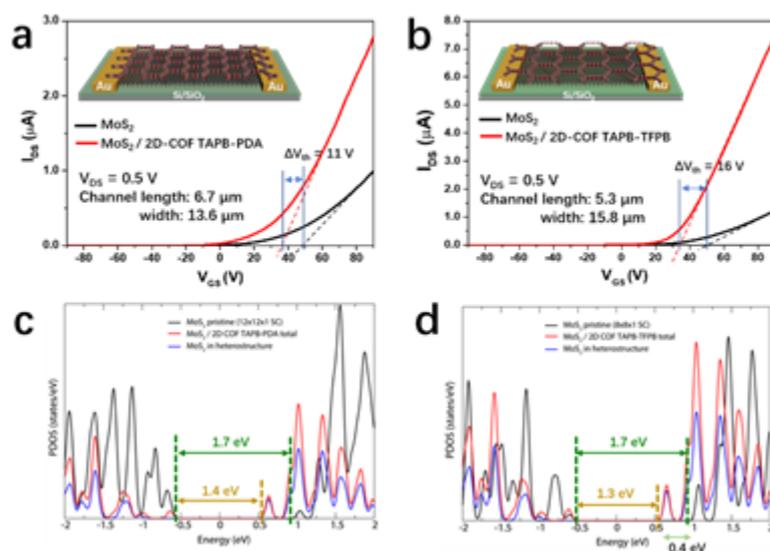


Figure 3. (a,b) Transfer characteristics of pristine monolayer MoS₂ FET devices before (black line) and after (red line) interfacing with (a) TAPB-PDA and (b) TAPB-TFPB based 2D-COFs. (c,d) Density of states (DOS) of MoS₂/2D-COF TAPB-PDA, in 12 x 12 unit cell (c) and MoS₂/2D-COF TAPB-TFPB, in 8 x 8 unit cell (d). Zero energy level is arbitrarily set to the middle of the band gap for comparison.

To bestow information on the band structure alignment caused by the charge transfer process, the electrical characteristics of the CVD MoS₂ based films were investigated by constructing FETs. Back-gate monolayer MoS₂ devices were fabricated by using thermally evaporated top Au electrodes, which exhibit Ohmic contact at room temperature. It is worth noting that the mixed monomer films limited the devices' current with a weak p-doping effect (Figure S16), while the covalently bonded 2D-COF films yielded an improvement in the devices' performance. **Figure 3a and 3b** compared the

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representative gate-dependent transport characteristics of monolayer MoS₂ devices with source-drain bias at V_{DS} = 500 mV. The pristine carrier density (n_e) in MoS₂ could be extracted from the formula: n_e = I_{DS}L/V_{DS}Wqμ. At V_{GS} = 0V, n_e was calculated as 5.72 × 10⁹ cm⁻² (Figure 2a) and 2.42 × 10⁹ cm⁻² (Figure 2b). The transfer curves were monitored before and after the 2D-COF film physisorption, revealing a significant shift of the threshold voltage (V_{th}) towards negative V_{GS}. In particular, the source-drain current (I_{DS}) was greatly enhanced upon interfacing with 2D-COF films. The n-type doping effect could be quantified by the threshold voltage shift (ΔV_{th}), which is linearly proportional with the change of carrier densities (Δn) (Equation 2). Here, ΔV_{th} was estimated to be 11 V for MoS₂/2D-COF TAPB-PDA and 16 V for MoS₂/2D-COF TAPB-TFPB, corresponding to a Δn of 1.04 × 10¹² cm⁻² and 1.51 × 10¹² cm⁻², respectively. The results recorded on five different devices for each vdWH type are summarized in Figure S18 and S19, revealing a good reproducibility. Moreover, compared to the mixed monomers film, the MoS₂/2D-COF vdWH device still performed well after thermal annealing at 470K (Figure S20), hence being compatible to back-end integration process temperatures.

The ideal MoS₂ / 2D-COF vdWH superlattices were modeled using density functional theory (DFT), as shown in Figure S18a and b. The periodicity of these two 2D-COFs hexagonal lattice was simulated as 2.56 nm and 3.82 nm, in accordance with our STM results (Figure 1b and 1c). The different charge density images (Figure S21c and d) indicated the electron transfer process from 2D-COF layer to MoS₂. The magnitude of electron transfer was calculated as 1.46 × 10¹² cm⁻² and 2.18 × 10¹² cm⁻² for TAPB-PDA and TAPB-TFPB containing MoS₂ / 2D COF vdWH, respectively. While the trend of the experimentally determined electron transfer values are in good agreement with the simulated ones, the former exhibited smaller absolute values because of the imperfect crystalline structure resulting from the interfacial synthesis of the 2D-COF films.

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Alongside, the density of states (DOS) simulation also provided insight into the charge transfer process in the vdWHs, as shown in **Figure 3c and 3d**. The comparison of the DOS maps of MoS₂ before (black) and after (red) 2D-COF physisorption reveals a ~ 0.3 eV energy shift towards lower energy values for MoS₂ conduction electrons in MoS₂/ 2D-COF TAPB-PDA heterostructure, and ~ 0.4 eV in MoS₂/ 2D-COF TAPB-TFPB heterostructure. The shift of conduction band induced an increased probability of exciting electrons, confirming that the n-type doping on MoS₂ originates from the charge transfer effect of 2D-COF film. On the same time, the band gap (E_g) reduced from 1.7 eV (pristine MoS₂) to 1.4 eV and 1.3 eV for MoS₂/ 2D-COF TAPB-PDA and MoS₂/ 2D-COF TAPB-TFPB, respectively.

More importantly, the interlayer coupling of the CVD MoS₂ with the 2D-COF film led to a major relative enhancement of the field-effect electron mobility (μ) extracted from I_{DS} - V_{GS} curves (equation 2). Our unoptimized devices comprising the MoS₂/ 2D-COF TAPB-PDA heterostructure (Figure 3a) exhibited a μ of 9.8 cm²V⁻¹s⁻¹, being notably larger than that in the pristine MoS₂ device (4.3 cm²V⁻¹s⁻¹). Similarly, the dressing of MoS₂ with the 2D-COF TAPB-TFPB film increased the μ from 5.2 cm²V⁻¹s⁻¹ to 21.1 cm²V⁻¹s⁻¹ (Figure 3b). The 2D-COF TAPB-TFPB could induce a much higher carrier mobility in monolayer MoS₂, which was also proved by simulation (Figure S23). Moreover, coating both sides of MoS₂ with 2D-COF films can further optimize the device's performance by enhancing the electron transfer process (Figure S24). The observed relative enhancement in field-effect mobility is noteworthy since typically the electron doping of MoS₂ resulting from its interfacing with a thin physisorbed organic molecular film is accompanied by a more modest increase in μ ^[32]. Greater changes in charge carrier density up to 5×10^{13} e⁻/cm² were observed when interfacing MoS₂ with a reduced form of benzyl viologen (BV) film, which was accompanied by a major increase in field-effect mobility. However, the BV doping of MoS₂ is accompanied by a semiconductor-to-semimetal phase transition, as evidenced by a loss in the field-

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effect modulation [33]. In our case, the vdWHs' FET devices could maintain a good $I_{\text{on}}/I_{\text{off}}$ ratio, which increased from 9.9×10^5 to 2.8×10^6 with 2D-COF TAPB-PDA's dressing, and from 1.2×10^6 to 7.4×10^6 with 2D-COF TAPB-TFPB's interfacing. By and large, the mobility of our MoS_2 FET devices displayed a substantial increase upon interfacing with 2D-COF film, while a not enormous charge carrier density change of $10^{12} \text{ e}^-/\text{cm}^2$ enabled to retain MoS_2 's semiconductor properties.

2.4. Monitoring the optical phonon energy in vdWHs

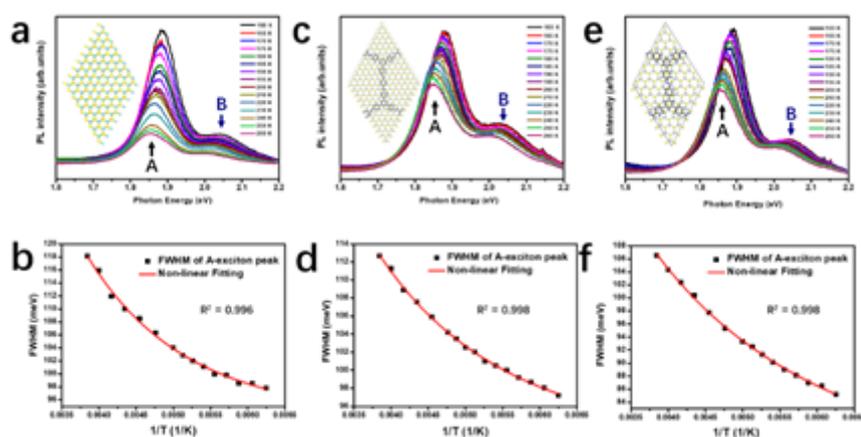


Figure 4. Temperature dependent PL spectra and plotted full width at half maximum (FWHM): (a,b) MoS_2 , (c,d) MoS_2 / 2D-COF TAPB-PDA heterostructure, and (e,f) MoS_2 / 2D-COF TAPB-TFPB heterostructure.

High energy phonon are known to scatter free carriers, thus affecting the carrier mobility of semiconductors[34]. Compared to the molecule assembly systems, the 2D-COFs have good robustness and stiffness, which can further improve MoS_2 's charge carrier mobility by minimizing the coupling between phonons and electrons.

The optical phonon energies of MoS_2 and MoS_2 / 2D-COF heterostructures have been quantified by

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temperature-dependent PL spectra measured above 160 K^[35]. **Figure 4a** shows that spectra of CVD MoS₂ monolayers transferred onto Si/SiO₂ substrates at increasing temperature exhibits a blue shift of both A and B exciton peaks and decreased peak intensity. The A-exciton peaks could be extracted after the detailed Lorentzian fitting of PL spectra, e.g., the monolayer MoS₂ PL spectra at 160 K (Figure S25). Meanwhile, the temperature-dependent peak-width broadening of A-exciton was plotted in **Figure 4b** and fitted using the independent Boson model^[36]. The contribution of acoustic phonon could be neglected within the temperature range from 160 K to 260 K, therefore the optical phonon dominates the line width broadening. Accordingly, the measured full width at half maxima (FWHM) data were fitted with the independent Boson model (equation 2), and the optical phonon energy was found as $\hbar\omega_{\text{op}} = 61.8 \pm 6.0$ meV. Our results are in excellent agreement with those obtained through theoretical calculation^[37]. The temperature dependent PL measurements were also carried out on the MoS₂ / 2D-COF vdWHs, as portrayed in **Figure 4c and 4e**. Compared to monolayer MoS₂, the heterostructure displayed a reduced decrease in the PL spectra intensity. More importantly, a significant reduction of $\hbar\omega_{\text{op}}$ was found after coated with 2D-COF film, as 48.2 ± 4.6 meV for MoS₂ / 2D-COF TAPB-PDA (**Figure 4d**) and 32.6 ± 7.1 meV for MoS₂/2D-COF TAPB-TFPB (**Figure 4f**). The decrease in the optical phonon energy represents a strong evidence for the suppression of the lattice vibration in MoS₂, which also indicates the suppression of phonon-electron interaction^[34b]. In the vdWHs, the difference in 2D-COF structure yielded a different density of COFs' molecules on MoS₂. Notably, 2D-COF TAPB-TFPB film with a smaller porous size had a stronger suppression effect on MoS₂'s lattice vibration, which could be related to a space confinement effect due to a large surface coverage. The related activation energy of A-exciton (E_{B}) was obtained via Arrhenius equation, detailed in Figure S26. A substantial drop of E_{B} after coating 2D-COF film could lead an increasing in the free carrier

population of MoS₂. As MoS₂/2D-COF heterostructures belonged to type II band alignment (Figure S13), a depletion region of mobile charge carriers was formed at the interface, which caused dissociation in the electron and hole energy levels on both side of the junction, resulting in a reduced exciton energy state compared to pristine MoS₂ crystal.

2.5. Temperature dependent carrier transport in vdWHs FET

Carrier scattering, originated from deviations from ideal lattice periodicity, can act as a damping process for carrier motion: ionized impurity scattering in low temperature range and lattice (phonon) scattering in high temperature range are the two main phenomena^[38]. To gain a deeper understanding on the scattering mechanism of electrons in our system, temperature-dependent mobility characteristics have been investigated.

Figure 5a displays the transfer characteristics of MoS₂ device measured from 10K to 300K. The device transfer curves are expressed in terms of the channel conductivity ($\sigma = I_{DS} \times W / L$) to facilitate the comparison with the vdWH-FET devices. With the increasing temperature the threshold voltage shifted towards negative values and the transfer current first increased then decreased^[39]. The corresponding mobility (μ) as a function of temperature was plotted in **Figure 5b**: the mobility increased with the decreasing temperature in the temperature range from 300K to 100K and almost saturated below 100K, in agreement with previous studies^[34c, 39c]. The ionized impurity scattering in the pristine MoS₂ at temperatures below 200K can be neglected. However, the mobility due to thermal lattice vibration scattering decreased with increasing temperature, as the phonon population follows the Bose-Einstein distribution. Figure 5b reveals that mobility (μ) evolution in the temperature region from 200K to 300K approximately follows the relation $\mu \propto T^{-\gamma}$, with $\gamma \sim 1.65$ being the phonon damping factor for pristine MoS₂ FET^[40].

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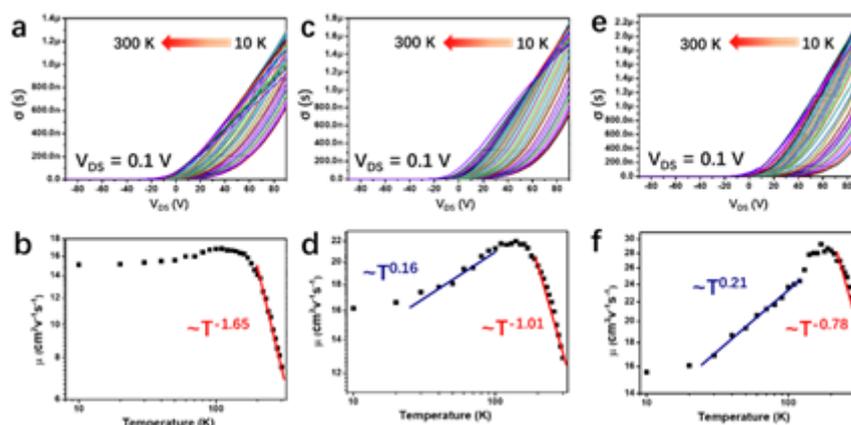


Figure 5. (a) Temperature dependent FET transfer curves of pristine monolayer MoS₂. (b) The mobility related to (a) as a function of temperature. (c) Temperature dependent FET transfer curves of MoS₂ / 2D-COF TAPB-PDA heterostructure. (d) The mobility related to (c) as a function of temperature. (e) Temperature dependent FET transfer curves of MoS₂ / 2D-COF TAPB-TFPB heterostructure. (f) the mobility related to (e) as a function of temperature.

The temperature dependent transfer characteristics of MoS₂ / 2D-COF vdWHs have been depicted in **Figure 5c and 5e**. Compared with the pristine MoS₂ device, the channel conductivity of the heterostructure displayed a significant improvement. Moreover, the mobilities of the heterostructure devices (**Figure 5d and 5f**) also increased with the decreasing temperature from 300 K to 100 K. However, the increase in the device mobility for heterostructure was more reduced when compared to the pristine MoS₂ device, as confirmed by a smaller fitted γ (~ 1.01 for MoS₂ / 2D-COF TAPB-PDA and ~ 0.78 for MoS₂ / 2D-COF TAPB-TFPB). Since the carrier mobility was dominated by the intensity of lattice (phonon) scattering in high temperature region, a small phonon damping factor (γ) could induce a high carrier mobility at room temperature^[39b]. MoS₂ / 2D-COF TAPB-TFPB vdWH yielded a more efficient suppression on MoS₂'s lattice vibration, in excellent agreement with the optical phonon energy results shown in Figure 4.

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The doping of MoS₂ with organic molecules always generates charged dopants that hinder charge transport. The charged impurity scattering was observed in the MoS₂/2D-COF vdWHs devices^[41]. Unlike the saturated case for pristine MoS₂, μ reached a maximum value at approximately 150K, and gradually slipped down at a temperature range below 100K, in accordance with the power function ($\mu \propto T^{-\gamma}$) with a negative value of γ . More specifically, γ was fitted as ~ 0.16 for MoS₂/ 2D-COF TAPB-PDA device (Figure 5d) and ~ 0.21 for MoS₂/ 2D-COF TAPB-TFPB device (Figure 5f), coinciding quite well with the stronger electron doping effect in MoS₂/ 2D-COF TAPB-PDA device. All the mobility behaviors implied the suppression of lattice scattering in high-temperature range and the enhanced dopant-induced scattering in low-temperature range for the vdWH devices^[42].

3. Conclusion

In this work, we demonstrated the fabrication of hybrid MoS₂/2D-COF vdWHs by dressing monolayer CVD MoS₂ with 2D-COF films, by achieving a long-range order functionalization of MoS₂ with strong interlayer coupling effects, leading to significantly improved charge transport properties of MoS₂. Optical and electrical analyses corroborated with DFT calculations revealed that the 2D-COF induces a charge transfer process to MoS₂. Through the spatially long-range ordered doping, the excess electrons transferred into the MoS₂ channel caused an enlargement in the free carriers' population by 10^{12} e⁻/cm². Moreover, the 2D-COF film led confinement effect to reduce the lattice vibration of MoS₂, which were confirmed via temperature-dependent optical and electrical characterizations. The optical phonon energy of MoS₂ almost halved in the case of MoS₂/ 2D-COF TAPB-TFPB vdWH, while the device's mobility in room temperature increased by four times.

Using 2D-COF film to periodically dope TMDCs provided a novel approach to developing high-

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performance TMDC electronics. Based on the large library of organic functional molecules, the 2D-COF structure could be ad-hoc designed for example with 2D-COF structures incorporating n-doped monomers to further boost the n-doping effect for high-performance (opto)electronics or responsive building blocks to impart responsiveness to multiple external stimuli, for application in light-sensing and photo-detection. Moreover, the mechanical stiffness and thermal dynamic stability of the 2D-COF opens perspectives towards the use of the novel vdWH in artificial e-skins and ultra-flexible devices for health monitoring and related smart technologies.

4. Methods

STM and AFM: STM measurements were performed by a Veeco scanning tunneling microscope (multimode Nanoscope III, Veeco). 200 nm thick Au (111) on mica was used as substrate for 2D-COF film coating. The employed STM tips were mechanically cut from a Pt/Ir wire (80 / 10, diameter 0.25 mm). The images were captured under ambient conditions. AFM images were obtained using a Bruker Dimension Icon set-up operating in air, in tapping mode, by using tip model TESPA-V2, tip stiffness K is 42 N m^{-1} .

XPS: X-ray photoelectron spectroscopy analyses were carried out with a Thermo Scientific K-Alpha X-ray photoelectron spectrometer. A basic chamber pressure of about 10^{-9} mbar. Aluminum anode was employed as the X-ray source (x-ray radiation of 1486 eV). All XPS spectra were calibrated using the C 1s peak at 284.8 eV as a reference. Peak-fitting and chemical qualification were performed using the Avantage software.

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FET fabrication and characterization: CVD MoS₂ flakes (Six Carbon Technology) were transferred onto SiO₂ substrates (270 nm SiO₂ thickness onto n-doped Si from Fraunhofer IPMS, Germany). Back-gated FET devices were fabricated by laser writer lithography, with Au source and drain electrodes thermally evaporated onto the patterned substrate. Warm acetone was used for the lift-off process, and the as-fabricated devices were annealed at 390K in vacuum to remove atmospheric adsorbates. The fabricated FET devices were measured in an N₂-filled glovebox with a probe station connected to a Keithley 2636A source-meter unit.

Temperature dependent measurements were carried out in a cryogenic probe station (Janis-CCR5-2) using a semiconductor parameter analyzer (Keithley 4200) with a vacuum degree of about 5×10^{-5} mbar.

The carrier mobility μ was determined from the following equation:

$$\mu = \frac{dI_{DS}}{dV_{DS}} \times \frac{L}{WC_iV_{DS}} \quad (2)$$

L and W are the channel length and width, and C_i is the insulator capacitance per unit of area.

The dopant-induced charge carrier density increase (Δn) was calculated from equation 2:

$$\Delta n = C_i \frac{\Delta V_{th}}{e} \quad (2)$$

Where ΔV_{th} is the difference in threshold voltage (V_{th}) before and after doping effect, and e is the elementary charge (1.6×10^{-19} C).

Raman and photoluminescence (PL) spectra: Raman and PL spectra were carried out in air by Renishaw inVia spectrometer equipped with 532 nm laser, and the wavenumber resolution was 1 cm⁻¹. The excitation power was kept below 1 mW to avoid the local heating damaged effects. Temperature-dependent experiments were recorded with the samples protected under inert nitrogen atmosphere, and low temperatures were applied with a Linkam TP95 temperature controller.

The independent Boson model equation:

$$\Gamma(T) = \Gamma_0 + \sigma T + \frac{\Gamma_0 p}{e^{\hbar\omega_0 p/k_B T} - 1} \quad (2)$$

In which Γ_0 is the inhomogeneous broadening contribution, σ is the exciton-acoustic phono interaction ($T > 0$, neglected), $\Gamma_0 p$ is exciton-optical phonon contribution, k_B is Boltzmann constant (8.617×10^{-5} eV/K), and $\hbar\omega_0 p$ is the optical phonon energy.

DFT calculations: Charge density calculations were performed by using the Vienna ab-initio Simulation Package (VASP)^[43]. The Perdew-Burke-Ernzerhof (PBE)^[44] functional was used to describe electron exchange and correlation. DFT-D2 method of Grimme^[45] was used in order to describe van der Waals forces. The Bader technique^[46] was adopted in order to determine the charge transfer in the structure. The kinetic energy cut-off for plane-wave expansion was set to 400 eV and the energy was minimized until its variation in the following steps became 10^{-4} eV. The Gaussian smearing method was employed for the total energy calculations and the width of the smearing was chosen as 0.05 eV. Total Hellmann-Feynman forces in the until was reduced to 10^{-3} eV/Å. (1,1,1) Γ -centered k-point samplings were used for the unit cells. 3000 grid points were used for electronic density of states calculations.

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Supporting Information

Supporting Information is available from the Wiley Online Library or from the author.

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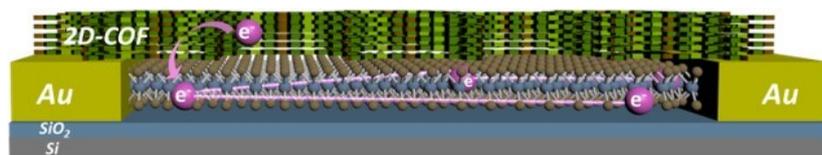
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The interfacing of monolayer MoS₂ with 2D-COF films determines a major enhancement in the charge transport through the 2D semiconductor. Electron doping intensity is amplified by the superlattice's long-range order, while the lattice vibration is suppressed by the high mechanical stiffness yielding a confinement effect. Our MoS₂/ 2D-COF van der Waals heterostructures represent a novel strategy to develop high-performance 2D electronics.

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Enhancing the Carrier Transport in Monolayer MoS₂ through Interlayer Coupling with 2D Covalent Organic Frameworks

ToC figure



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